

Semiconductors
High-reliability discrete products and engineering services since 1977

## 2N3879

NPN SILICON POWER TRANSISTORS

## FEATURES

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available as non-RoHS (Sn/Pb plating), standard, and as RoHS by adding "-PBF" suffix.

MAXIMUM RATINGS

| Ratings | Symbol | 2N3879 | Unit |
| :--- | :---: | :---: | :---: |
| Collector-Emitter Voltage | $\mathrm{V}_{\text {CEO }}$ | 75 | Vdc |
| Collector-Base Voltage | $\mathrm{V}_{\text {CBO }}$ | 120 | Vdc |
| Emitter-Base Voltage | $\mathrm{V}_{\text {EBO }}$ | 7.0 | Vdc |
| Base Current | $\mathrm{I}_{\mathrm{B}}$ | 5.0 | Adc |
| Collector Current | $\mathrm{II}_{\mathrm{C}}$ | 7.0 | Adc |
| Total Power Dissipation $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}^{(1)}$ | $\mathrm{P}_{\mathrm{D}}$ | 35 | W |
| Operating \& Storage Junction Temperature Range | $\mathrm{T}_{\mathrm{J}, \mathrm{T}_{\text {stg }}}$ |  |  |
| Maximum Thermal Resistance Junction to Case | $\mathrm{R}_{\text {өJ }}$ | -65 to +200 | ${ }^{\circ} \mathrm{C}$ |

Note 1: Derate linearly @ $200 \mathrm{~mW} /{ }^{\circ} \mathrm{C}$ for $\mathrm{T}_{\mathrm{A}}>25^{\circ} \mathrm{C}$
ELECTRICAL CHARACTERSITICS ( $\mathrm{T}_{\mathrm{A}}=25^{\circ} \mathrm{C}$ unless otherwise specified)

| Characteristics | Symbol | Min. | Max. | Unit |
| :---: | :---: | :---: | :---: | :---: |
| OFF CHARACTERISTICS |  |  |  |  |
| Collector-Emitter Breakdown Voltage $\mathrm{I}_{\mathrm{c}}=200 \mathrm{~mA}$ | $\mathrm{V}_{\text {(BR) }}$ Ceo | 75 | - | Vdc |
| Collector-Emitter Cutoff Current $V_{C E}=50 \mathrm{Vdc}$ | Iceo | - | 5.0 | mAdc |
| Collector-Emitter Cutoff Current $\mathrm{V}_{\mathrm{CE}}=50 \mathrm{Vdc}, \mathrm{~V}_{\mathrm{BE}}=1.5 \mathrm{~V}$ | Icex | - | 4.0 | mAdc |
| Collector-Base Cutoff Current $\mathrm{V}_{\mathrm{CB}}=120 \mathrm{Vdc}$ | $I_{\text {cbo }}$ | - | 25 | mAdc |
| Emitter-Base Cutoff Current $\mathrm{V}_{\mathrm{EB}}=7.0 \mathrm{Vdc}$ | Iebo |  | 10 | mAdc |
| Forward Current Transfer Ratio $\begin{aligned} & \mathrm{I}_{\mathrm{c}}=0.5 \mathrm{Adc}, \mathrm{~V}_{\mathrm{CE}}=5.0 \mathrm{Vdc} \\ & \mathrm{I}_{\mathrm{C}}=4.5 \mathrm{Adc}, \mathrm{~V}_{\mathrm{CE}}=5.0 \mathrm{Vdc} \\ & \mathrm{I}_{\mathrm{c}}=4.0 \mathrm{Adc}, \mathrm{~V}_{\mathrm{CE}}=2.0 \mathrm{Vdc} \end{aligned}$ | $h_{\text {fe }}$ | $\begin{aligned} & 40 \\ & 20 \\ & 12 \end{aligned}$ | $\begin{gathered} 80 \\ 100 \end{gathered}$ | - |
| Collector-Emitter Saturation Voltage $\mathrm{I}_{\mathrm{C}}=4.0 \mathrm{Adc}, \mathrm{I}_{\mathrm{B}}=0.4 \mathrm{Adc}$ | $\mathrm{V}_{\text {cE(sat) }}$ | - | 1.2 | Vdc |
| Base-Emitter Saturation Voltage $\mathrm{I}_{\mathrm{c}}=4.0 \mathrm{Adc}, \mathrm{I}_{\mathrm{B}}=0.4 \mathrm{Adc}$ | $\mathrm{V}_{\text {BE(sat) }}$ | - | 2.0 | Vdc |
| Base-Emitter On Voltage $\mathrm{I}_{\mathrm{C}}=4.0 \mathrm{Adc}, \mathrm{~V}_{\mathrm{CE}}=2.0 \mathrm{~V}$ | $\mathrm{V}_{\text {be(on) }}$ |  | 1.8 | Vdc |
| DYNAMIC CHARACTERISTICS |  |  |  |  |
| Magnitude of Common Emitter Small-Signal Short Circuit Forward Current Transfer Ratio $\mathrm{I}_{\mathrm{C}}=0.5 \mathrm{Adc}, \mathrm{~V}_{\mathrm{CE}}=4.0 \mathrm{Vdc}, \mathrm{f}=100 \mathrm{kHz}$ | $1 h_{\text {FE }} \mathrm{l}$ | 4.0 | 20 | - |



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| Characteristics | Symbol | Min. | Max. | Unit |
| :---: | :---: | :---: | :---: | :---: |
| Output Capacitance $V_{C B}=10 \mathrm{Vdc}, \mathrm{I}_{\mathrm{E}}=0,100 \mathrm{kHz} \leq \mathrm{f} \leq 1.0 \mathrm{MHz}$ | Cobo | - | 300 | pF |
| SWITCHING CHARACTERISTICS |  |  |  |  |
| Turn-On Time $\mathrm{V}_{\mathrm{cc}}=30 \mathrm{Vdc}, \mathrm{I}_{\mathrm{C}}=4.0 \mathrm{Adc}, \mathrm{I}_{\mathrm{B}}=40 \mathrm{mAdc}$ | $\mathrm{t}_{\text {on }}$ | - | 0.44 | $\mu \mathrm{s}$ |
| Turn-Off Time $\mathrm{V}_{\mathrm{CC}}=30 \mathrm{Vdc}, \mathrm{I}_{\mathrm{C}}=4.0 \mathrm{Adc}, \mathrm{I}_{\mathrm{B}}=-\mathrm{I}_{\mathrm{B}}=40 \mathrm{mAdc}$ | $\mathrm{t}_{\text {off }}$ | - | 1.2 | $\mu \mathrm{s}$ |
| SAFE OPERATING AREA |  |  |  |  |
| Dc Tests $\mathrm{T} \mathrm{c}=25^{\circ} \mathrm{C}, 1 \text { cycle, } \mathrm{t}=1.0 \mathrm{~s}$ <br> Test 1 $\mathrm{V}_{\mathrm{CE}}=5.0 \mathrm{Vdc}, \mathrm{I}_{\mathrm{C}}=7.0 \mathrm{Adc}$ <br> Test 2 $\mathrm{V}_{\mathrm{CE}}=28 \mathrm{Vdc}, \mathrm{I}_{\mathrm{C}}=500 \mathrm{mAdc}$ <br> Test 3 $\mathrm{V}_{\mathrm{CE}}=40 \mathrm{Vdc}, \mathrm{Ic}_{\mathrm{c}}=500 \mathrm{mAdc}$ <br> Test 4 $\mathrm{V}_{\mathrm{CE}}=75 \mathrm{Vdc}, \mathrm{I}_{\mathrm{C}}=100 \mathrm{mAdc}$ |  |  |  |  |

Note 1: Pulse Test: Pulse Width $=300 \mu s$, Duty Cycle $\leq 2.0 \%$
MECHANICAL CHARACTERISTICS

| Case | TO-66 |
| :--- | :--- |
| Marking | Alpha-numeric |
| Polarity | See below |



| Dim | TO-66 |  |  |  |
| :---: | :---: | :---: | :---: | :---: |
|  | Inches |  | Millimeters |  |
|  | Min | Max | Min | Max |
| BL | 1.205 | 1.280 | 30.60 | 32.50 |
| CD | 0.445 | 0.557 | 11.303 | 14.148 |
| CH | 0.257 | 0.284 | 6.540 | 7.220 |
| LL | 0.374 | 0.413 | 9.500 | 10.50 |
| BW | 0.680 | 0.727 | 17.26 | 18.46 |
| LD | 0.030 | 0.036 | 0.760 | 0.920 |
| HT | 0.054 | 0.065 | 1.380 | 1.650 |
| MHS | 0.951 | 0.976 | 24.16 | 24.78 |
| S1 | 0.545 | 0.614 | 13.84 | 15.60 |
| HD | 0.131 | 0.154 | 3.320 | 3.920 |
| PS | 0.191 | 0.210 | 4.860 | 5.340 |

